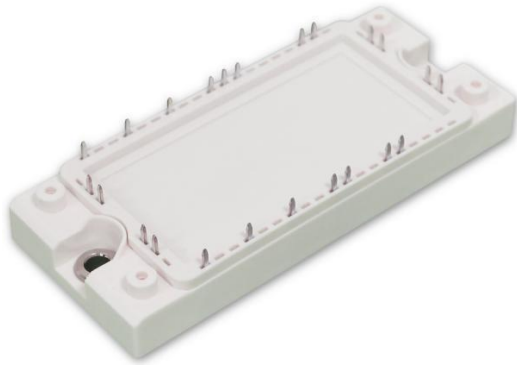


## IGBT Modules



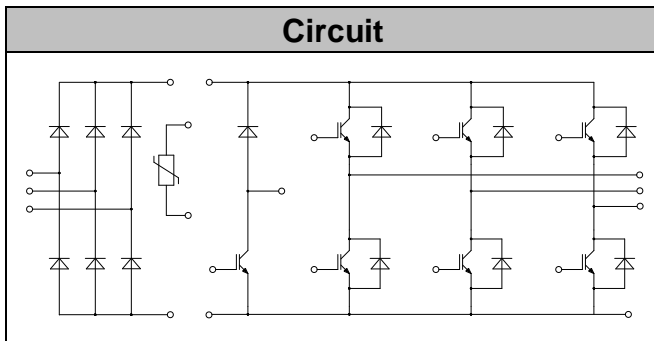
$V_{CES}$  1200V  
 $I_c$  50A

### Applications

- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)

### Features

- Low switching losses
- Low  $V_{CE(sat)}$  with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Maximum junction temperature 175°C



## ● IGBT- inverter

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_c=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	$I_c$	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	50	A
Repetitive Peak Collector Current	$I_{CRM}$	$t_p=1ms$	100	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25^{\circ}C$	$\pm 20$	V
Total Power Dissipation	$P_{tot}$	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	288	W



## ● IGBT- inverter

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.7mA, T_{vj}=25^{\circ}C$	5.2	5.8	6.4	V
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.90		V
		$I_C=50A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.20		
		$I_C=50A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.32		
Gate Charge	$Q_G$			0.35		uC
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		2.60		nF
Reverse Transfer Capacitance	$C_{res}$			0.10		nF
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=50A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=20\Omega$ $T_{vj}=25^{\circ}C$		41		ns
Rise Time	$t_r$			48		ns
Turn-off Delay Time	$t_{d(off)}$			160		ns
Fall Time	$t_f$			244		ns
Energy Dissipation During Turn-on Time	$E_{on}$			5.92		mJ
Energy Dissipation During Turn-off Time	$E_{off}$			3.39		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=50A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=20\Omega$ $T_{vj}=150^{\circ}C$		45		ns
Rise Time	$t_r$			50		ns
Turn-off Delay Time	$t_{d(off)}$			169		ns
Fall Time	$t_f$			302		ns
Energy Dissipation During Turn-on Time	$E_{on}$			6.87		mJ
Energy Dissipation During Turn-off Time	$E_{off}$			3.73		mJ
SC Data	$I_{sc}$	$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C,$ $V_{CC}=900V, V_{CEM} \leq 1200V$		200		A



## ● Diode-inverter

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25^{\circ}C$	1200	V
Continuous DC Forward Current	$I_F$		50	A
Repetitive Peak Forward Current	$I_{FRM}$	$t_p=1ms$	100	A
$I^2t$ -value	$I^2t$	$V_R=0V, t_p=10ms, T_{vj}=125^{\circ}C$	560	A <sup>2</sup> s
		$V_R=0V, t_p=10ms, T_{vj}=150^{\circ}C$	480	

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	$V_F$	$I_F=50A, T_{vj}=25^{\circ}C$		1.85		V
		$I_F=50A, T_{vj}=125^{\circ}C$		1.70		
		$I_F=50A, T_{vj}=150^{\circ}C$		1.62		
Recovered Charge	$Q_{rr}$	$I_F=50A$		4.39		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600V$ $-di_F/dt=1000A/\mu s$		31		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=25^{\circ}C$		1.35		mJ
Recovered Charge	$Q_{rr}$	$I_F=50A$		6.65		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600V$ $-di_F/dt=1000A/\mu s$		33		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=150^{\circ}C$		2.10		mJ



## ● IGBT-brake-chopper Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	$I_C$	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	35	A
Repetitive Peak Collector Current	$I_{CRM}$	$t_p=1ms$	70	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25^{\circ}C$	$\pm 20$	V
Total Power Dissipation	$P_{tot}$	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	227	W

## Characteristic values

Parameter	Symbol	Conditions	Value			Unit	
			Min.	Typ.	Max.		
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.4mA, T_{vj}=25^{\circ}C$	5.2	5.8	6.4	V	
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=35A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.95		V	
		$I_C=35A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.15			
		$I_C=35A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.25			
Gate Charge	$Q_G$			0.27		$\mu C$	
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		2.00		nF	
Reverse Transfer Capacitance	$C_{res}$			0.07		nF	
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA	
Turn-on Delay Time	$t_{d(on)}$	$I_C=35A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=27\Omega$ $T_{vj}=25^{\circ}C$		30		ns	
Rise Time	$t_r$			40		ns	
Turn-off Delay Time	$t_{d(off)}$				151		ns
Fall Time	$t_f$				257		ns
Energy Dissipation During Turn-on Time	$E_{on}$				3.50		mJ
Energy Dissipation During Turn-off Time	$E_{off}$				2.43		mJ



Turn-on Delay Time	$t_{d(on)}$	$I_C=35A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=27\Omega$ $T_{vj}=150^\circ C$	33	ns
Rise Time	$t_r$		44	ns
Turn-off Delay Time	$t_{d(off)}$		158	ns
Fall Time	$t_f$		274	ns
Energy Dissipation During Turn-on Time	$E_{on}$		4.13	mJ
Energy Dissipation During Turn-off Time	$E_{off}$		2.75	mJ
SC Data	$I_{sc}$		$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^\circ C,$ $V_{CC}=900V, V_{CEM} \leq 1200V$	150

## ● Diode-Brake-Chopper

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25^\circ C$	1200	V
Continuous DC Forward Current	$I_F$		15	A
Repetitive Peak Forward Current	$I_{FRM}$	$t_p=1ms$	30	A
I <sup>2</sup> t-value	$I^2t$	$V_R=0V, t_p=10ms, T_{vj}=125^\circ C$	16.0	A <sup>2</sup> s
		$V_R=0V, t_p=10ms, T_{vj}=150^\circ C$	14.0	

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	$V_F$	$I_F=15A, T_{vj}=25^\circ C$		2.00		V
		$I_F=15A, T_{vj}=125^\circ C$		1.80		
		$I_F=15A, T_{vj}=150^\circ C$		1.70		
Recovered Charge	$Q_{rr}$	$I_F=15A$		1.20		uC
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600V$ $-di_F/dt=550A/\mu s$		10		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=25^\circ C$		0.35		mJ
Recovered Charge	$Q_{rr}$	$I_F=15A$		1.60		uC
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600V$ $-di_F/dt=550A/\mu s$		15		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=150^\circ C$		1.20		mJ



## ● Diode-Rectifier

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25^{\circ}C$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_C=100^{\circ}C$	65	A
Maximum RMS Current at Rectifier Output	$I_{RMSM}$	$T_C=100^{\circ}C$	110	A
Surge Forward Current	$I_{FSM}$	$V_R=0V, t_p=10ms, T_{vj}=45^{\circ}C$	850	A
$I^2t$ -value	$I^2t$	$V_R=0V, t_p=10ms, T_{vj}=45^{\circ}C$	3610	A <sup>2</sup> s

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	$V_F$	$I_F=50A, T_{vj}=125^{\circ}C$		1.0		V
Reverse Current	$I_R$	$T_{vj}=125^{\circ}C, V_R=1600V$			1.5	mA

## ● NTC-Thermistor

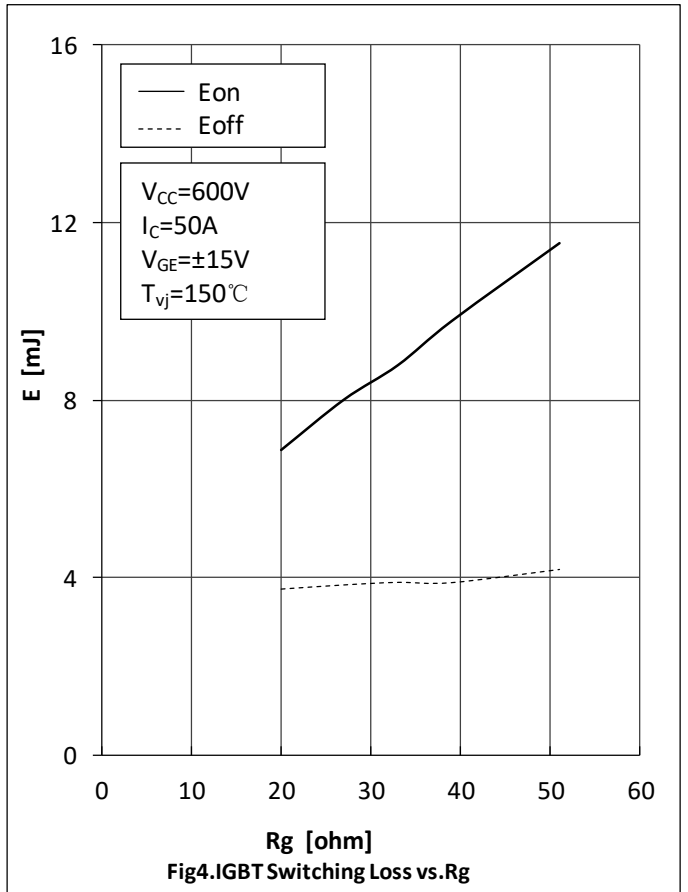
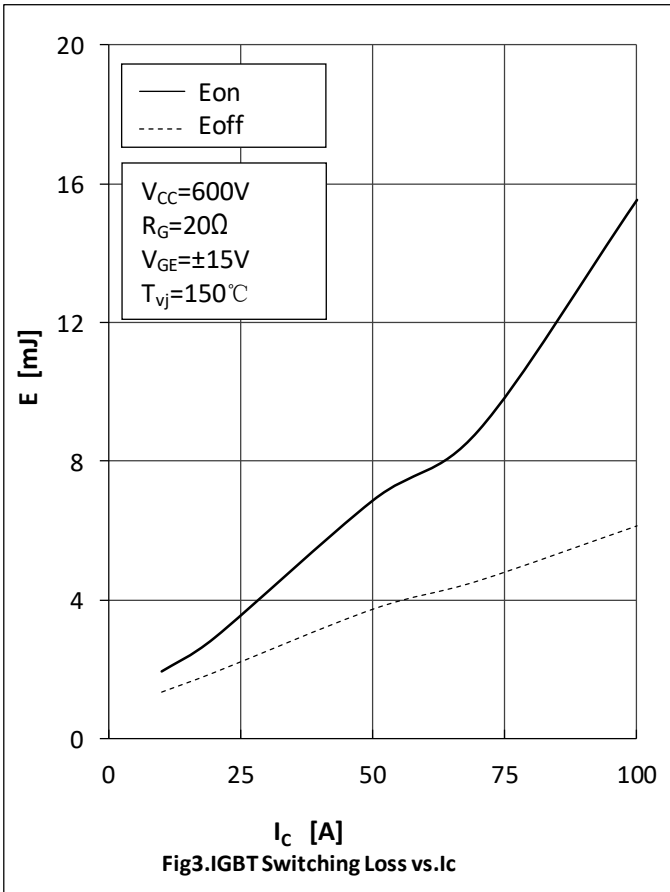
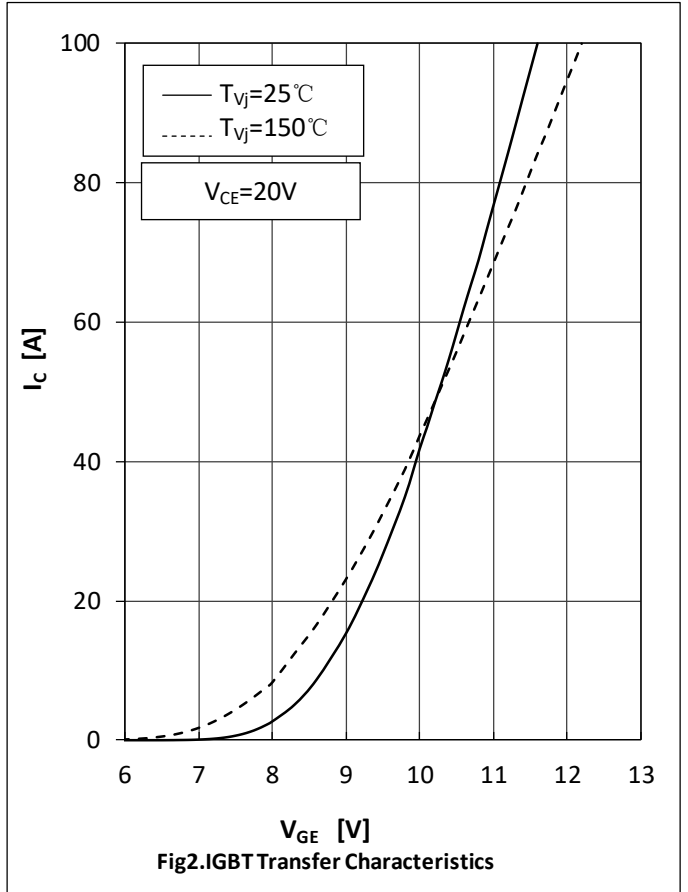
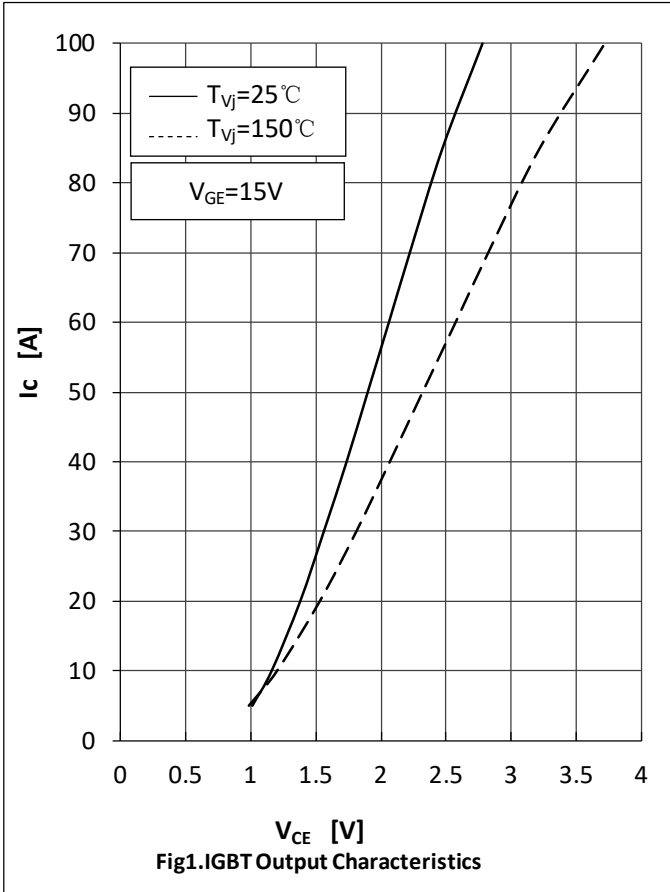
### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	$R_{25}$			5.0		k $\Omega$
Deviation of R100	$\Delta R/R$	$T_C=100, R_{100}=493.3\Omega$	-5		5	%
Power Dissipation	$P_{25}$				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

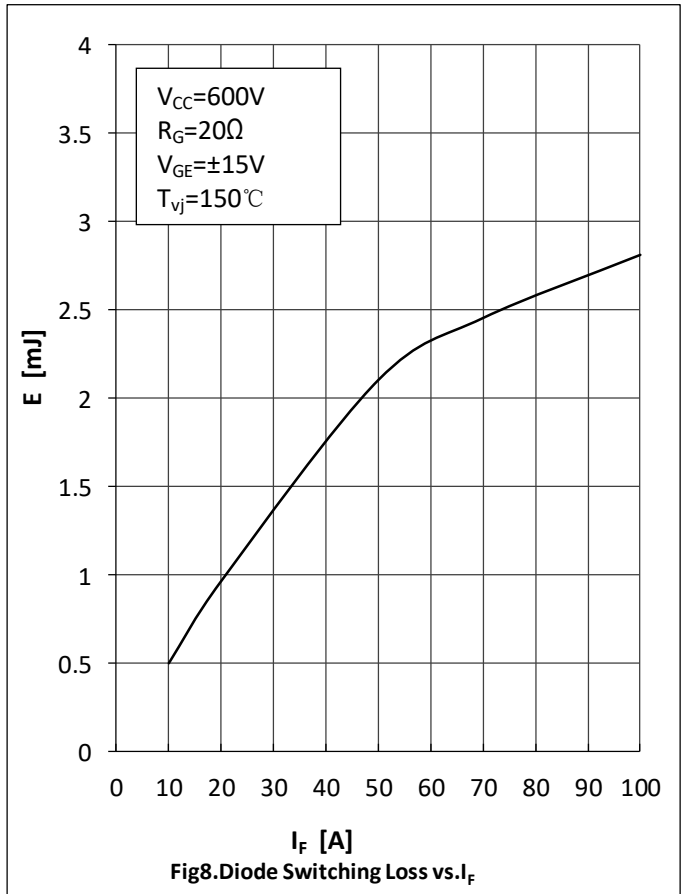
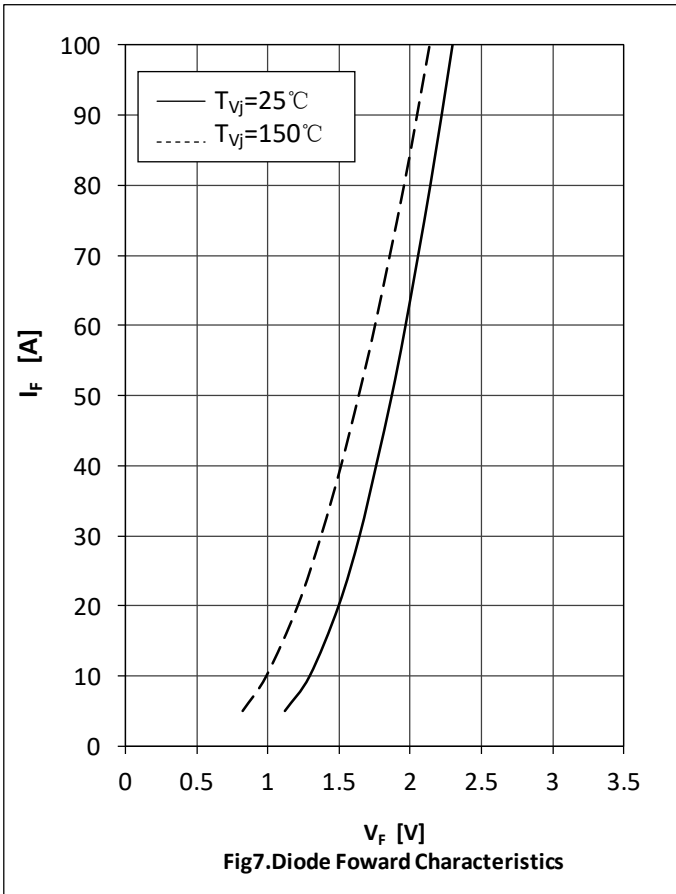
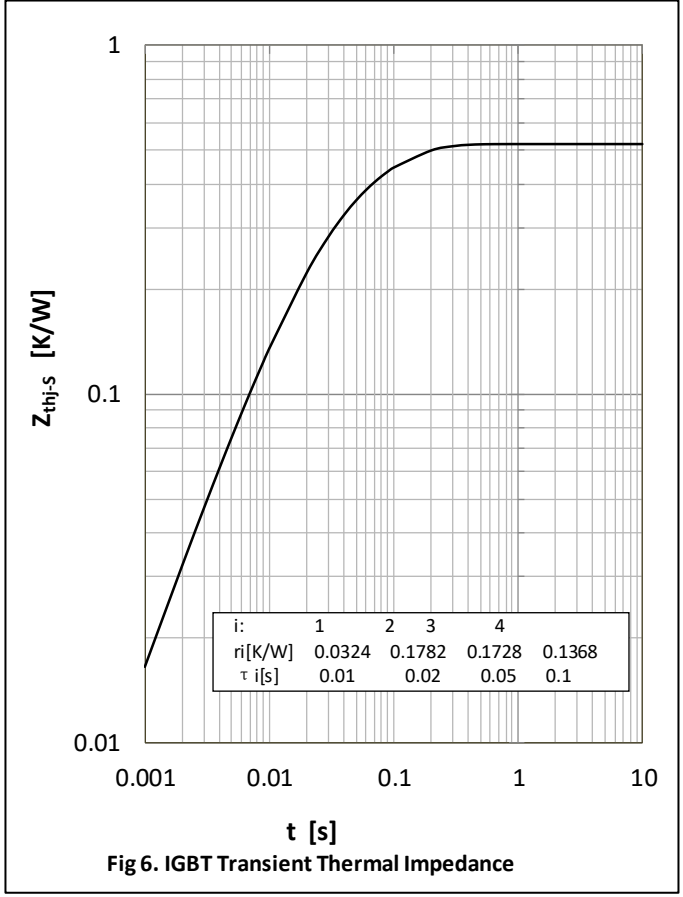
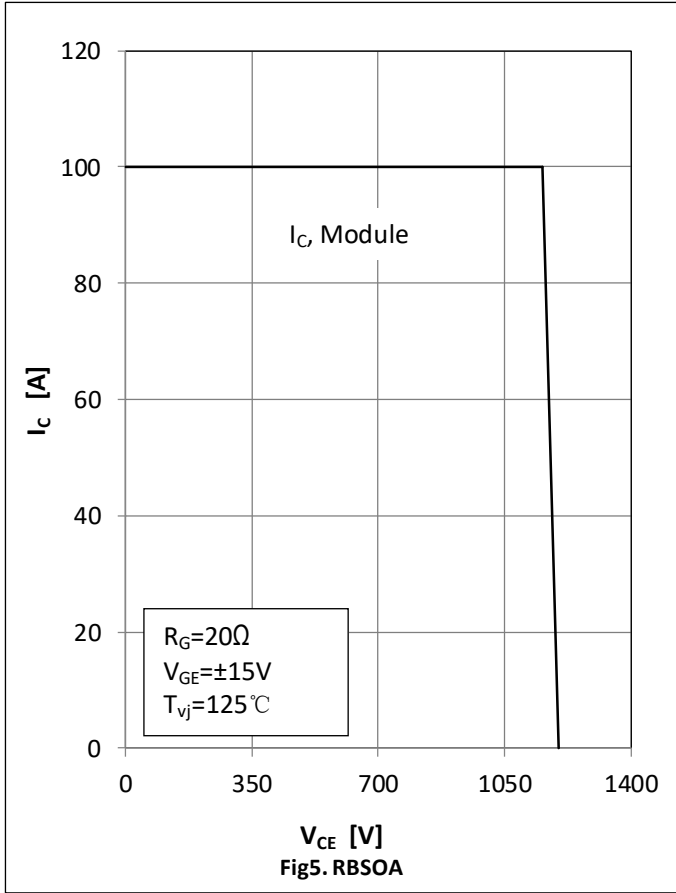


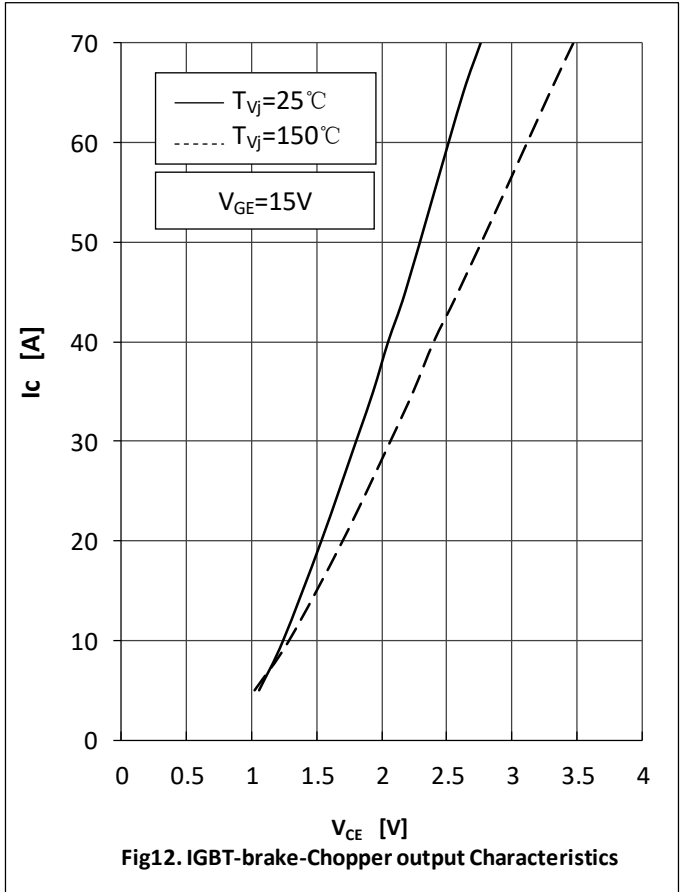
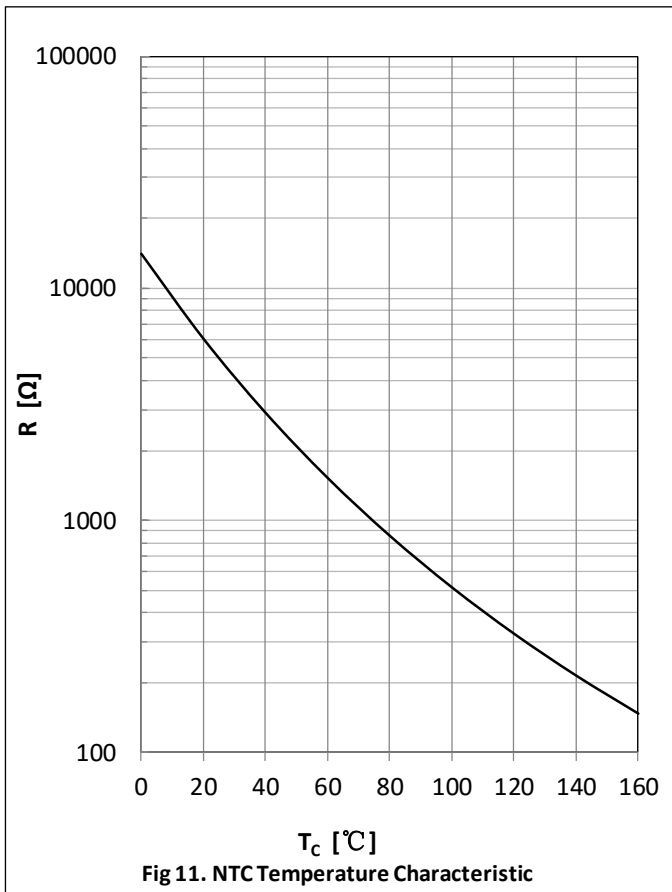
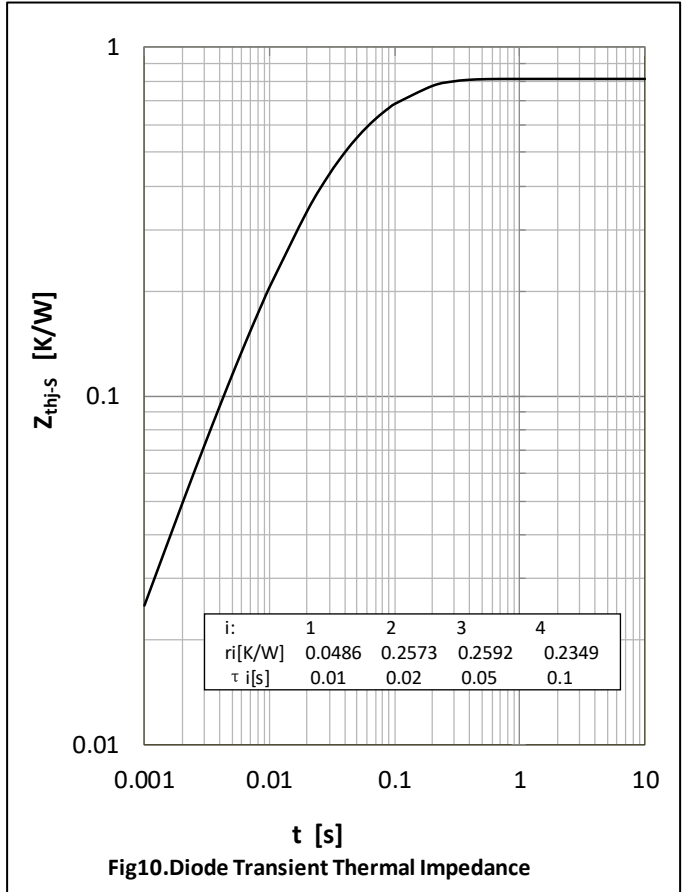
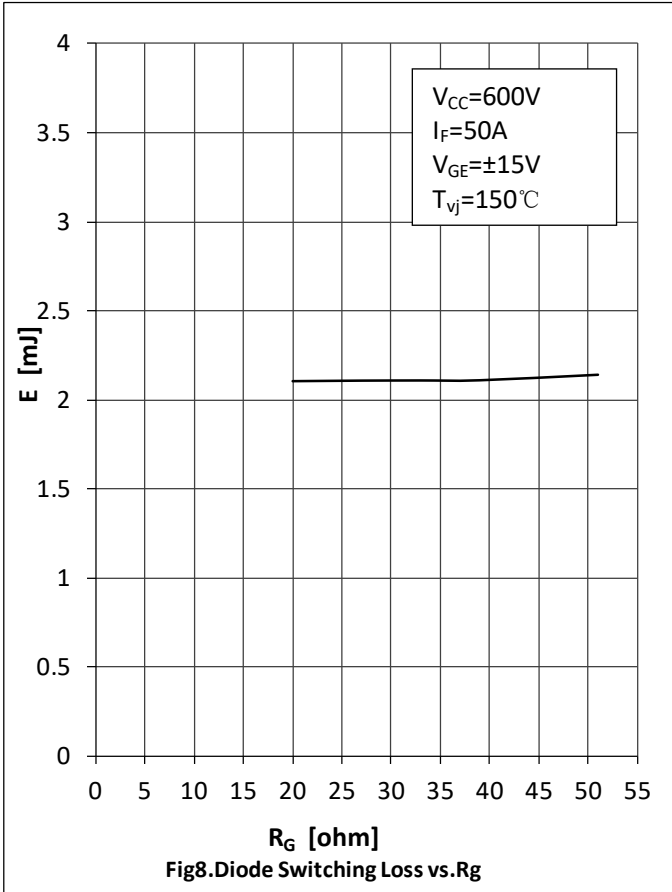
● **Module Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise specified

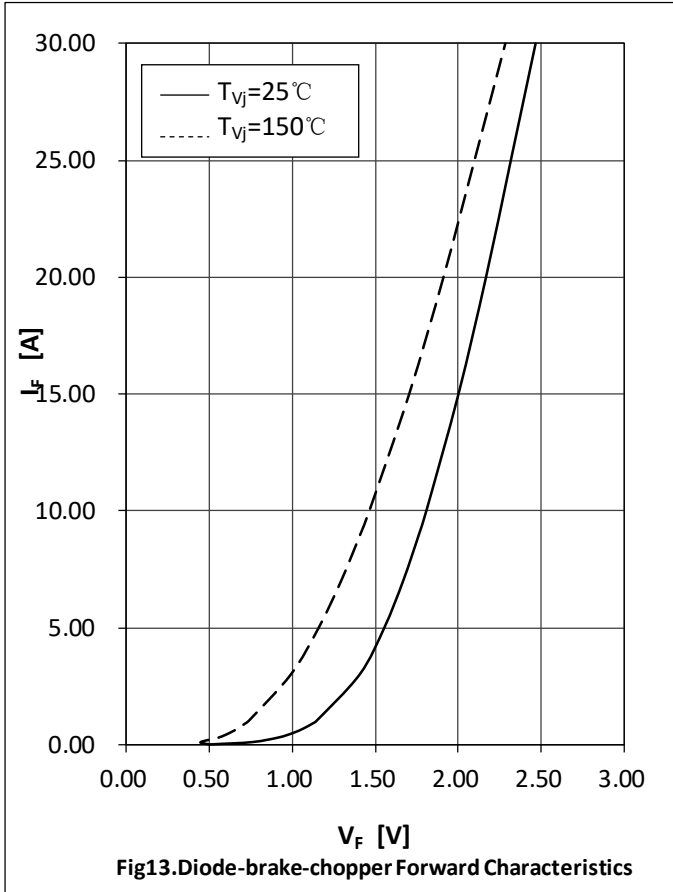
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	$V_{\text{isol}}$	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	$T_{\text{jmax}}$				175	$^\circ\text{C}$
Operating Junction Temperature	$T_{\text{vj op}}$		-40		150	$^\circ\text{C}$
Storage Temperature	$T_{\text{stg}}$		-40		125	$^\circ\text{C}$
Stray-inductance-module	$L_{\text{SCE}}$			40		nH
Module lead resistance, terminals-chip	$R_{\text{CC}'+\text{EE}}$	$T_C=25^\circ\text{C}$ , per switch		4.0		m $\Omega$
	$R_{\text{AA}'+\text{CC}'}$			3.0		
Thermal Resistance Junction-to Case	$R_{\theta\text{JC}}$	per IGBT-inverter		0.52		K/W
		per Diode-inverter		0.81		
		per IGBT-brake-chopper		0.66		
		per Diode-chopper		1.50		
		per Diode-rectifier		0.64		
Thermal Resistance Case-to Sink	$R_{\theta\text{CS}}$	per IGBT-inverter		0.29		K/W
		per Diode-inverter		0.44		
		per IGBT-brake-chopper		0.32		
		per Diode-chopper		0.33		
		per Diode-rectifier		0.70		
		per Module		0.009		
Module-to-Sink Torque	$M_s$		3.0		6.0	N·m
Weight of Module	G			180		g



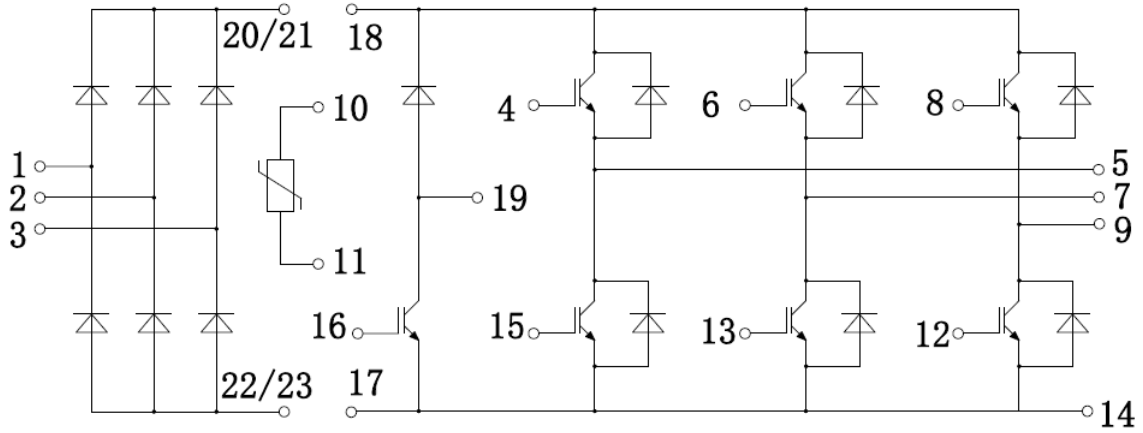




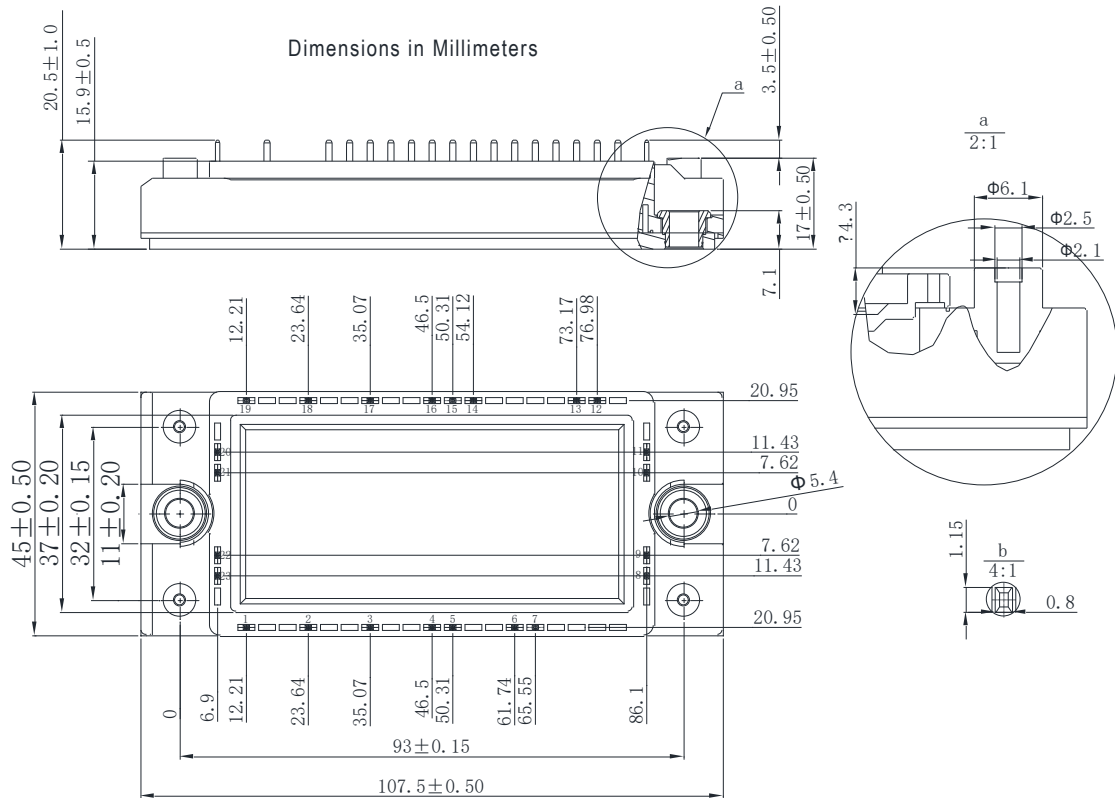




## ● Circuit Diagram



## ● Package Outline Information





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